## NSN 5961-00-168-8389

Semiconductor Device Set - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5961-00-168-8389
Inclosure Material:
Glass
Overall Length:
0.240 inches all transistor and 0.260 inches all transistor
Terminal Length:
0.500 inches all transistor
Overall Diameter:
0.335 inches all transistor and 0.370 inches all transistor
Internal Configuration:
Junction contact all transistor
Electrode Internally-electrically Connected To Case:
Collector all transistor
Internal Junction Configuration:
Npn all transistor
Component Function Relationship:
Matched
Component Name And Quantity:
2 transistor
Mounting Method:
Terminal all transistor
Semiconductor Material:
Silicon all transistor
Voltage Rating In Volts Per Characteristic:
60.0 collector to base voltage/static/emitter open all transistor and 30.0 collector to emitter voltage/static/base open all transistor and 3.5
emitter to base voltage, static, collector open all transistor
Current Rating Per Characteristic:
400.00 milliamperes collector current, dc all transistor
Power Rating Per Characteristic:
2.9 watts total power dissipation all transistor
Maximum Operating Tempurature Per Measurement Point:
200.0 degrees celsius junction all transistor
Test Data Document:
95542-3600-s-0046 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing
etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing)
Terminal Type And Quantity:
3 uninsulated wire lead all transistor
Specification Data:
95542-958-033 manufacturers source control
Shelf Life:
N/a

No

**Unit Of Measure:** 

Demilitarization:

## NSN 5961-00-168-8389

Semiconductor Device Set - Page 2 of 2



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